

# HIGH TEMPERATURE ICs



## For Harsh Environments

### Packages:

- Ceramic SOIC (CS)
- Ceramic DIP (D)
- Plastic SOIC (S)
- Gull Wing (H)
- J Leaded (J)
- Plastic PLCC (PL)
- Plastic DIP Module (PD)
- Leadless SLCC (Y)
- Ceramic Through-Hole (CT)

### Temperature:

- Extended Temperature -55° C to +180° C (ET)
- High Temperature -55° C to +200° C (HT)

### FLASH

Density	Max Temp	Org	Part No.	Vcc	Speed	Type
8/16Gb	+180° C	–	TTZ(8/16)GM08PD (Module)	2.7-3.6V	–	NAND Parallel
8/16Gb	+180° C	–	TTZ4GM(16/32)PL (Module)	2.7-3.6V	–	NAND Parallel
4Gb	+180° C	–	TTZ4G08	2.7-3.6V	–	NAND Parallel
1Gb	+180° C	–	TTZ251024 (Consult Factory)	2.7-3.3V	10MHz	SPI
512Mb	+180° C	–	TTZ25M512CT (Module)	2.7-3.3V	10Mhz	SPI
512Mb	+200° C	–	TTZ25512	2.7-3.3V	10Mhz	SPI
256Mb	+200° C	–	TTZ25M256CT (Module)	2.7-3.3V	10Mhz	SPI
256Mb	+200° C	–	TTZ25256	2.7-3.3V	10Mhz	SPI
128Mb	+200° C	–	TTZ25M128CT (Module)	2.7-3.3V	10Mhz	SPI
128Mb	+200° C	–	TTZ25128	2.7-3.3V	10Mhz	SPI
64Mb	+200° C	–	TTZ2564	2.7-3.3V	10Mhz	SPI

### PARALLEL EEPROM

Density	Max Temp	Org	Part No.	Vcc	Speed (ns)	Type
4Mb	+180° C	512Kx8	TTE28M040P (Module)	5V	120,150,175	Parallel
2Mb	+180° C	256Kx8	TTE28M020P (Module)	5V	120,150,175	Parallel
1Mb	+180° C	128Kx8	TTE28C010	5V	120,150,175	Parallel
1Mb	+200° C	128Kx8	TTE28HT010	5V	150,200,250	Parallel

### SERIAL EEPROM

Density	Max Temp	Org	Part No.	Vcc	Speed	Type
2Mb	+180° C	–	TTE25M2048PD (Module)	2.7-5.5V	10MHz	SPI
1Mb	+180° C	–	TTE25M1024PD (Module)	2.7-5.5V	10MHz	SPI
1Mb	+180° C	–	TTE25C1024	2.7-5.5V	10MHz	SPI
1Mb	+200° C	–	TTE25C1024 (Consult Factory)	2.7-5.5V	10MHz	SPI
512Kb	+200° C	–	TTE25C512	2.7-5.5V	10MHz	SPI
256Kb	+200° C	–	TTE25C256	2.7-5.5V	10MHz	SPI
256Kb	+200° C	–	TTE24C256	2.7-5.5V	400KHz	I2C
64Kb	+200° C	–	TTE25C64	2.7-5.5V	10MHz	SPI
64Kb	+200° C	–	TTE24C64	2.7-5.5V	400KHz	I2C

Consult factory for additional densities and module configurations

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### ASYNCHRONOUS SRAM

Density	Max Temp	Org	Part No.	Vcc	Speed (ns)	Type
8Mb	+200° C	512Kx16	TTS512KX16LV	2.7-3.6V	20	Parallel
8Mb	+200° C	512Kx16	TTS512KX16	5V	20	Parallel
16Mb	+200° C	1Mx16	TTS1MX16LV	2.7-3.6V	20	Parallel
16Mb	+200° C	1Mx16	TTS1MX16	5V	20	Parallel

### SWITCH MODE CONTROLLER

Function	Max Temp	Input Voltage	Part No.	Efficiency
CURRENT MODE CONTROLLER	+200° C	10-120V	TT9110	HIGH
CURRENT MODE CONTROLLER	+180° C	10-450V	TT9120	HIGH

### REAL TIME CLOCK

Function	Max Temp	Interface	Part No.	Vcc	Current	Oscillator
ALL CALENDAR FUNC.	+180° C	I <sup>2</sup> C	TTA365SET	2.7V-5.5V	.65µA	External 32.768KHz
ALL CALENDAR FUNC.	+200° C	I <sup>2</sup> C	TTA365CSHT	2.7V-5.5V	.65µA	External 32.768KHz

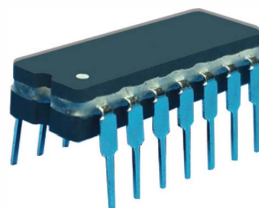
### SUPERVISORY CIRCUIT- COMING SOON

#### CUSTOM SOI Capability



#### SUPERVISORY CIRCUIT

- Multiple Voltages single package
- Open Drain Output
- Hold Reset for 350ms (Typical)
- + 200° C Operation
- Ceramic SOIC Package



#### SWITCH MODE CONTROLLERS

- 9120: 10-450V Input Range
- 9110: 10-120V Input Range
- Current Mode Controller
- High Efficiency
- +200° C Max. Operating Temp
- Plastic and Ceramic SOIC and Ceramic CerDIP Packages

#### REAL TIME CLOCK

- Provides Year, Month, Day, Weekday, Hours, Minutes and Seconds Based on a 32.768KHz Quartz Crystal
- 1.8v to 5.5v Operation
- Low Backup Current; Typical .65µA
- I<sup>2</sup>C Bus Interface
- Alarm and Timer Functions
- +200° C Operation
- Ceramic SOIC Package

Consult factory for additional densities and module configurations